MCC/21/ M.SC./SEM.-III/PHS/1

ESTD 201

Total pages: 02

PG CBCS M.Sc. Semester- III Examination, 2022 PHYSICS

PAPER: PHS 303B

(APPLIED ANALOG ELECTRONICS-I & APPLIED DIGITAL ELECTRONICS-I)

Full Marks: 40

Time: 2 Hours

Write the answer for each unit in separate sheet

UNIT- PHS 303B.1

APPLIED ANALOG ELECTRONICS-I

GROUP-A

1. Answer any <u>TWO</u> from the following questions:

2. Answer any TWO from the following questions:

 $2 \times 2 = 4$

- a) What is totem pole configuration?
- b) How to quickly identify whether a log amplifier is working properly or not?
- c) What is an active filter? Draw the ideal response of the band pass and band stop filter.
- d) What will be the typical input voltage range of an anti-log or exponential amplifier and why?

GROUP-B

$2 \times 4 = 8$

- a) Derive the output voltage expression of a BJT differential pair
- b) Explain four quadrants analog multiplier using a details circuit diagram and its working principle.
- c) What is a zero-crossing detector? Explain its operation using a clear diagram.
- d) Design an active low pass filter and find the cut-off frequency expression of the same?

GROUP-C

3. Answer any <u>ONE</u> from the following questions:

1×8=8

- a) Derive output voltage expression of a typical instrumentation amplifier. What is the basic difference between a typical differential amplifier and an instrumentation amplifier? Write a few applications of an instrumentation amplifier.
- b) What is the transfer function of an active filter? Draw typical characteristics of a Chebyshev and Butterworth active filter. Derive the cutoff frequency of a fourth-order type-I Chebyshev filter.

(P.T.O.)

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UNIT- PHS 303B.2 APPLIED DIGITAL ELECTRONICS-I

GROUP-A

1. Answer any <u>TWO</u> of the following questions:

- a) Why Emitter Coupled Logic (ECL) is the fastest among all other logic family members?
- b) What is the difference between TDMA and FDMA?
- c) Draw a CMOS inverter circuit.
- d) What is ARPANET?

GROUP-B

2. Answer any TWO of the following questions:

3. Answer any <u>ONE</u> of the following questions:

- a) Explain the operation of 2- inputs NAND gate using CMOS circuit?
- b) Explain how ISDN works? Differentiate SRAM and DRAM.
- c) What are the ratioed and ratioless logic? Draw and explain in brief voltage transfer characteristics (VTC) for both cases. (1+3)
- d) A certain memory has a capacity of 32×16. How many bits are there in each word? How many words are being stored and how many memory cells does this memory contain? (1+3)

GROUP-C

1×8=8

 $2 \times 4 = 8$

- a) Explain the operation of the 6T SRAM cell and 1T1C DRAM cell in detail? Explain the operation of 2- inputs NAND gate using totem pole circuit. What do you mean by Schottky TTL? Why is it faster than standard TTL?
- b) Explain the operation of 2- inputs NAND gate using totem pole circuit. What do you mean by Schottky TTL? Why is it faster than standard TTL?





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